

Microsemi

Power Matters[™]

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Overview **Diagrams**

Collector to Emitter Saturation Voltage

DC Current Gain	HFE	25.0	0		100.00	
Maximum Electrical Rating		Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)		V _{BR(CBO)}			100.00	V
Collector Current (dc)		I _C			16.00	Α
Collector-Emitter Voltage (Base Open)		V _{CEO}			100.00	V
Emitter-Base Voltage (Collector Open)		V _{EBO}			7.00	V
Power Dissipation, Total		P _T			200.00	W

V_{CE(sat)}

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor
- $\bullet \ \ \, \text{Non-Radiation Hardened Devices} \ \bullet \ \, \text{Transistors} \ \bullet \ \, \text{BJT(BiPolar Junction Transistor)} \ \bullet \ \, \text{NPN Transistor}$

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